

IN THE ABSTRACT

Replace the current abstract with the following abstract.

Discloses is a metal-oxide-compound semiconductor field effect transistor structure, method of making, and method of using, the structure comprising: a nitride compound semiconductor wafer structure having an upper surface; a gate insulator structure comprising a first layer and a second layer; wherein said first layer comprises oxygen and indium, said first layer in contact with said upper surface; and wherein said second layer comprises at least one insulating compound.